

isc N-Channel MOSFET Transistor

FDB035AN06A0

• FEATURES

- With TO-263(D2PAK) packaging
- Single pulse and repetitive pulse
- High speed switching
- Low miller charge
- Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operationz

• APPLICATIONS

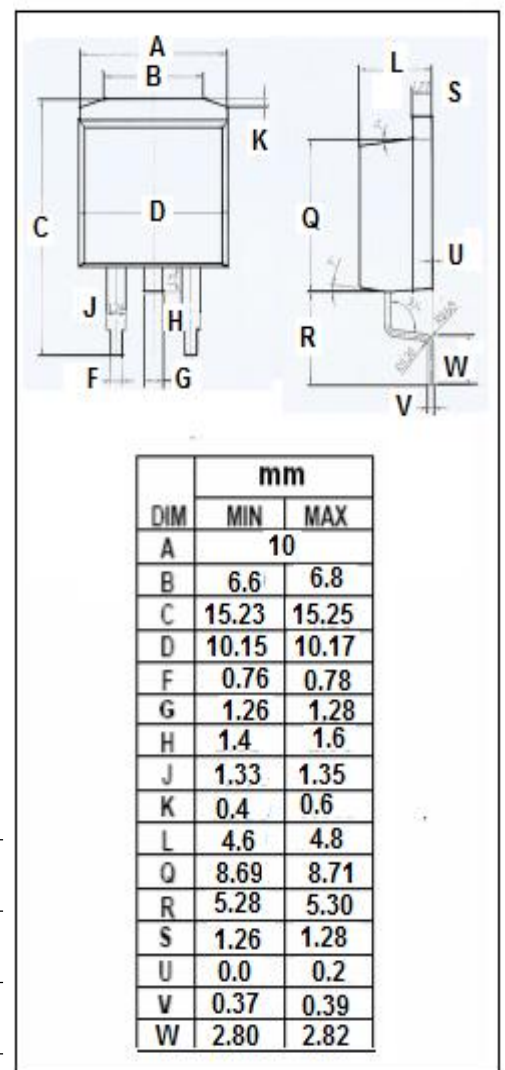
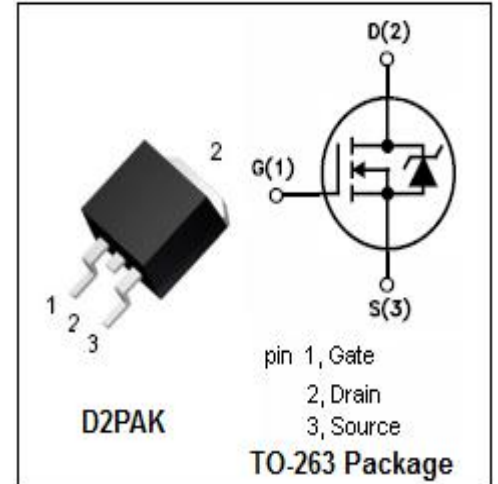
- PFC stages, hard switching PWM stages and resonant switching
- PC Silverbox, Adapter, LCD & PDP TV
- Lighting, Server, Telecom and UPS

• ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|---|----------|--------------------|
| V_{DS} | Drain-Source Voltage | 60 | V |
| V_{GS} | Gate-Source Voltage | ± 20 | V |
| I_D | Drain Current-Continuous@ $T_c=25^{\circ}\text{C}$ $T_c=100^{\circ}\text{C}$ | 80 22 | A |
| I_{DM} | Drain Current-Single Pulsed | 400 | A |
| P_D | Total Dissipation | 310 | W |
| T_j | Operating Junction Temperature | -55~175 | $^{\circ}\text{C}$ |
| T_{stg} | Storage Temperature | -55~175 | $^{\circ}\text{C}$ |

• THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|----------------|---------------------------------------|------|----------------------|
| $R_{th(ch-c)}$ | Channel-to-case thermal resistance | 0.48 | $^{\circ}\text{C/W}$ |
| $R_{th(ch-a)}$ | Channel-to-ambient thermal resistance | 62 | $^{\circ}\text{C/W}$ |



isc N-Channel MOSFET Transistor**FDB035AN06A0****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|---------------------|--------------------------------|---|-----|-----|----------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D = 0.25mA | 60 | | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =±20V; I _D =0.25mA | | | 4 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =80A | | 6.5 | 7.1 | mΩ |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} = ±20V; V _{DS} = 0V | | | ±1 | μA |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} = 60V; V _{GS} = 0V@T _j =25°C T _j =150°C | | | 1 250 | μA |
| V _{SDF} | Diode forward voltage | I _{SD} =80A, V _{GS} = 0 V | | | 1.25 | V |

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